

Application No.: 10/777,469

Docket No.: 09852/0200879-US0

Claim 6 (original): The method of forming a Si-containing thin film according to claim 2, comprising steps of vaporizing the organic Si-containing compound and an organic hafnium compound, thermally decomposing the vaporized organic Si-containing compound and the vaporized organic hafnium compound, and allowing the decomposed compounds to react with O₂ gas.

Claim 7 (original): The method of forming a Si-containing thin film according to claim 1, wherein the formed Si-containing thin film does not contain Cl.

Claim 8 (original): The method of forming a Si-containing thin film according to claim 1, wherein forming the film is conducted at a temperature not greater than 700°C.

Claim 9 (original): The method of forming a Si-containing thin film according to claim 1, wherein the film forming is performed in 5 minutes or less.

Claim 10 (original): The method of forming a Si-containing thin film according to claim 1, wherein the thickness of the Si-containing thin film is 50 nm or less.

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